

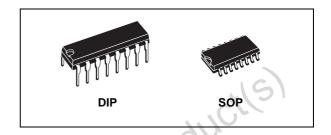


8 BIT ADDRESSABLE LATCH

- SERIAL DATA INPUT ACTIVE PARALLEL OUTPUT
- STORAGE REGISTER CAPABILITY -MASTER CLEAR
- CAN FUNCTION AS DEMULTIPLEXER
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- INPUT LEAKAGE CURRENT $I_1 = 100$ nA (MAX) AT $V_{DD} = 18$ V $T_A = 25$ °C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



HCF4099B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. HCF4099B, an 8-bit addressable latch, is a serial-input, parallel output storage register that can perform a variety of functions. Data is input to a particular bit in the latch when that bit is addressed (by means of input A0, A1, A2) and when WRITE DISABLE is at a low level. When

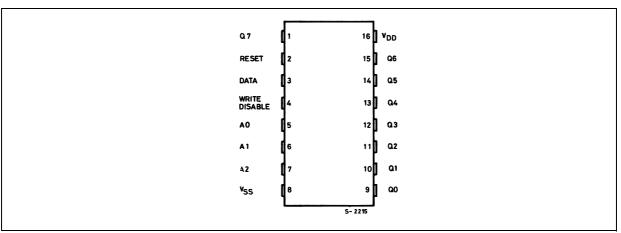


ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4099BEY	
SOP	HCF4099BM1	HCF4099M013TR

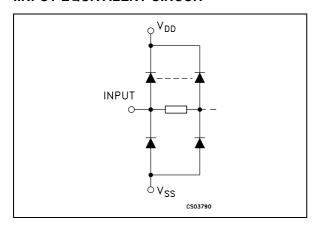
WRITE DISABLE is high, data entry is inhibited; however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs. A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer; the bit that is addressed has an active output which follows the data input, while all unaddressed bits are held to a logic "0" level.

PIN CONNECTION



October 2002 1/14

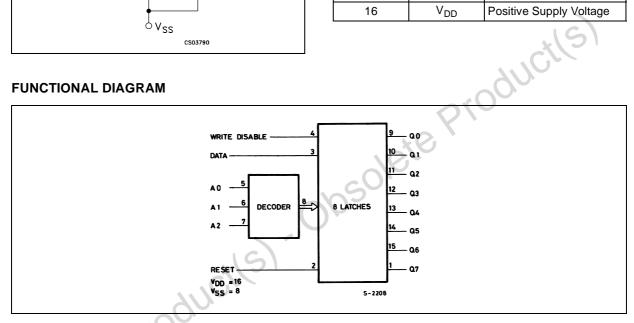
IINPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
5, 6, 7	A0 to A2	Address Inputs
9, 10, 11, 12, 13, 14, 15, 1	Q0 to Q7	Latch Outputs
3	DATA	Data Inputs
2	RESET	Reset Input
4	WRITE DISABLE	Write Disable Input
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

FUNCTIONAL DIAGRAM



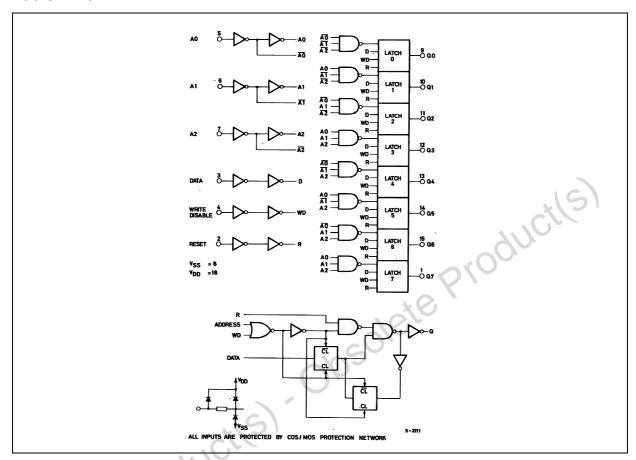
TRUTH TABLE

48	SELECT INPUTS		LATOU ADDRESSED
CC	В	Α	LATCH ADDRESSED
CO, L	L	L	Q0
D L	L	Н	Q1
L	Н	L	Q2
L	Н	Н	Q3
Н	L	L	Q4
Н	L	Н	Q5
Н	Н	L	Q6
Н	Н	Н	Q7

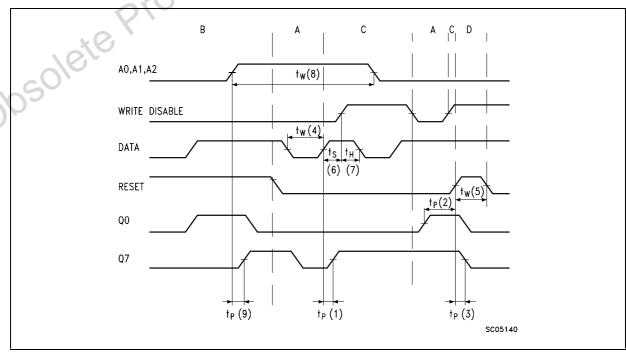
INP	UTS	OUTPUTS OF	EACH OTHER	FUNCTION
WRITE DISABLE	RESET	ADDRESSED LATCH	OUTPUT	FUNCTION
L	L	D	Qi0	ADDRESSABLE LATCH
L	Н	Qi0	Qi0	MEMORY
Н	L	D	L	DEMULTIPLEXER
Н	Н	L	L	CLEAR ALL BITS TO "0"

D: The level at the data input; Q_{i0} The level before the indicated steady state input conditions were established, (i=0, 1,...7)

LOGIC DIAGRAM



TIMING CHART



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C
Obsole	ate Productis). Obsole ste		

DC SPECIFICATIONS

			Test Cond	litions	i				Value				
Symbol	Parameter	Vı	٧o	Io	V _{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(μA)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.04	5		150		150	
		0/10			10		0.04	10		300		300	μΑ
		0/15			15		0.04	20		600		600	μΛ
		0/20			20		0.08	100		3000		3000	
V _{OH}	High Level Output	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95	16	
V_{OL}	Low Level Output	5/0		<1	5		0.05			0.05	X	0.05	1
	Voltage	10/0		<1	10		0.05			0.05	10	0.05	V
		15/0		<1	15		0.05			0.05	O,	0.05	
V_{IH}	High Level Input		0.5/4.5	<1	5	3.5			3.5	0^{\vee}	3.5		
	Voltage		1/9	<1	10	7		4	7		7		V
			1.5/18.5	<1	15	11			11		11		
V_{IL}	Low Level Input		0.5/4.5	<1	5			1.5		1.5		1.5	
	Voltage		9/1	<1	10			3		3		3	V
			1.5/18.5	<1	15		0,	4		4		4	
I _{OH}	Output Drive	0/5	2.5		5	-1.36	-3.2		-1.1		-1.1		
	Current	0/5	4.6		5	-0.44	-1		-0.36		-0.36		mA
		0/10	9.5		10	-1.1	-2.6		-0.9		-0.9		1117 \
		0/15	13.5		15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink	0/5	0.4)	5	0.44	1		0.36		0.36		
	Current	0/10	0.5		10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5		15	3.0	6.8		2.4		2.4		
II	Input Leakage Current	0/18	any in	out	18		±10 ⁻⁵	±0.1		±1		±1	μΑ
C _I	Input Capacitance		any in	out			5	7.5					pF

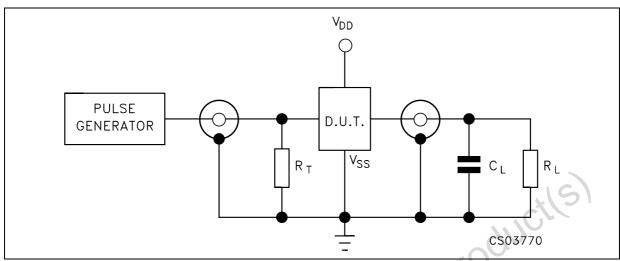
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} =5V, 2V min. with V_{DD} =10V, 2.5V min. with V_{DD} =15V

 $\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \ (\textbf{T}_{amb} = 25^{\circ} \textbf{C}, \ \textbf{C}_{L} = 50 \text{pF}, \ \textbf{R}_{L} = 200 \text{K}\Omega, \ \textbf{t}_{r} = \textbf{t}_{f} = 20 \text{ ns})$

	_		Test Condition			Value (*)			
Symbol	Parameter	V _{DD} (V)	See Timing Chart	Min.	Тур.	Max.			
t _{PLH} t _{PHL}	Propagation Delay Time	5			200	400			
	(Data to Output)	10	(1)		75	150	ns		
		15			50	100			
t _{PLH} t _{PHL}	Propagation Delay Time	5			200	400			
	(Write Disable to Output)	10	(2)		80	160	ns		
		15			60	120			
t _{PLH} t _{PHL}	Propagation Delay Time	5			225	450			
	(Address to Output)	10	(9)		100	200	ns		
		15			75	150	1		
t _{PHL}	Propagation Delay Time	5			175	350			
	(Reset to Output)	10	(3)	7.	80	160	ns		
		15		$\triangle O$	65	130			
t _{THL} t _{TLH}	Transition Time	5		O'	100	200			
	(any output)	10		ŀ	50	100	ns		
		15	* O. `		40	80			
t _W	Pulse Wldth (Data)	5	10.	200	100				
		10	(4)	100	50		ns		
		15	1250	80	40				
t _W	Pulse Wldth (Address)	5	00	400	200				
		10	(8)	200	100		ns		
		15		125	65				
t _W	Pulse Wldth (Reset)	5		150	75				
		10	(5)	75	40		ns		
	(15		50	25				
t _{setup}	Setup Time	5		100	50				
	(Data to Write Disable)	10	(6)	50	25		ns		
	010	15		35	20				
t _{hold}	Hold Time	5		150	75				
	(Data to Write Disable)	10	(7)	75	40		ns		
	(C)	15		50	25				

^(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT

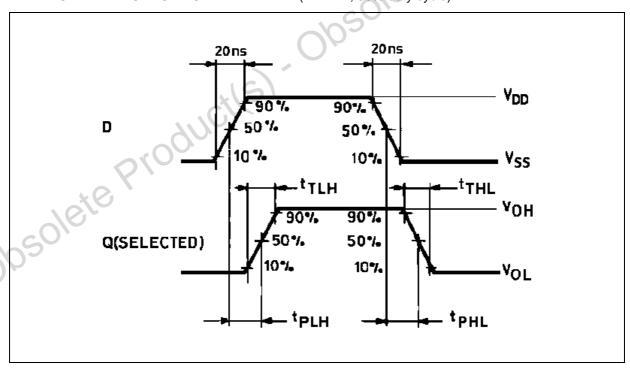


C_L = 50pF or equivalent (includes jig and probe capacitance)

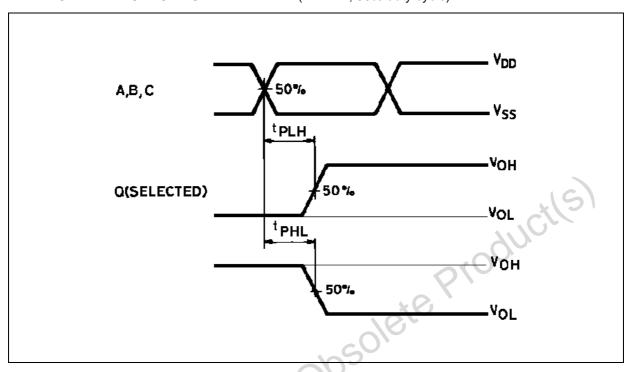
 $R_1 = 200 K\Omega$

 $R_T^2 = Z_{OUT}$ of pulse generator (typically 50 Ω)

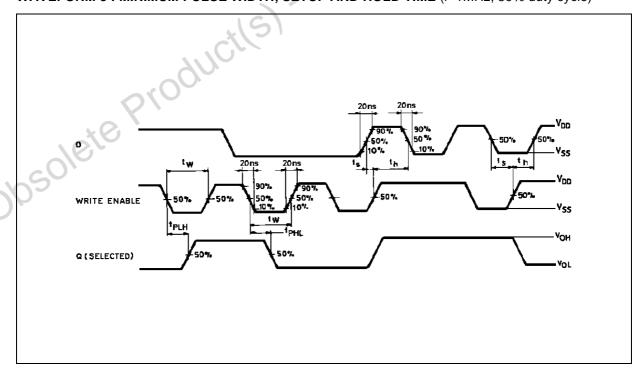
WAVEFORM 1: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



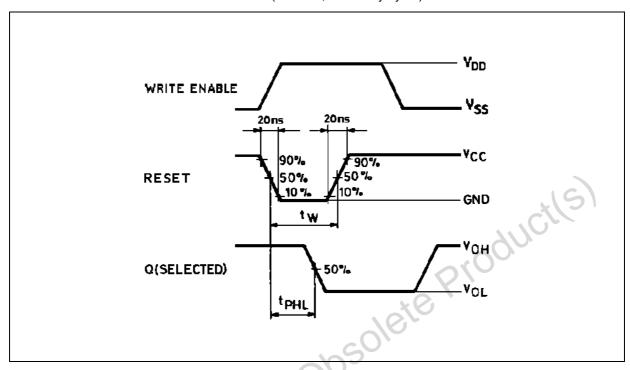
WAVEFORM 2: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



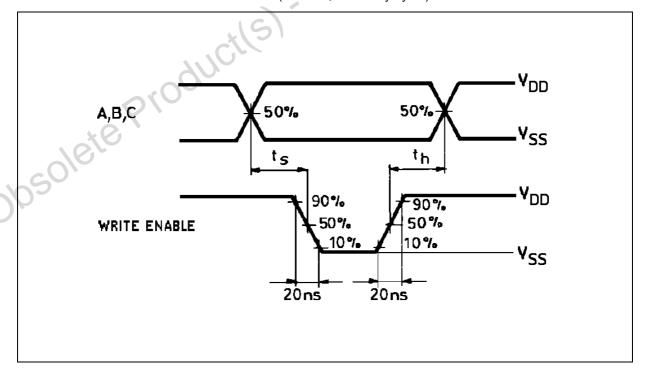
WAVEFORM 3 : MINIMUM PULSE WIDTH, SETUP AND HOLD TIME (f=1MHz; 50% duty cycle)



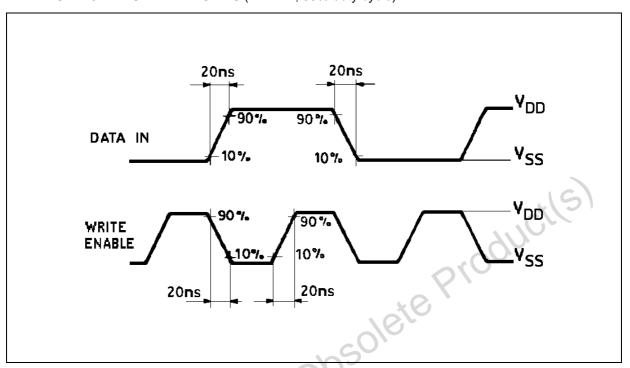
WAVEFORM 4: MINIMUM PULSE WIDTH (f=1MHz; 50% duty cycle)



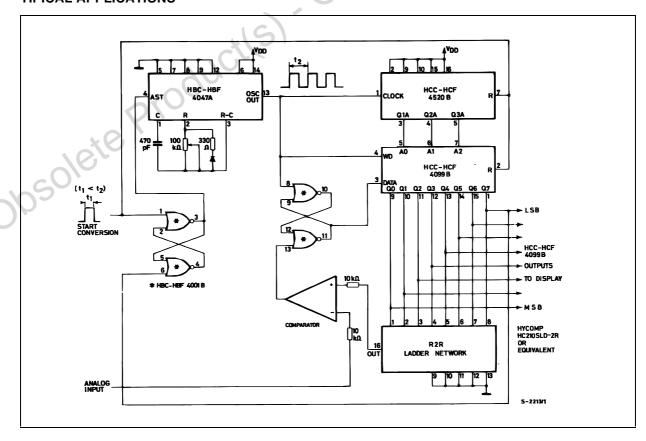
WAVEFORM 5: SETUP AND HOLD TIME (f=1MHz; 50% duty cycle)



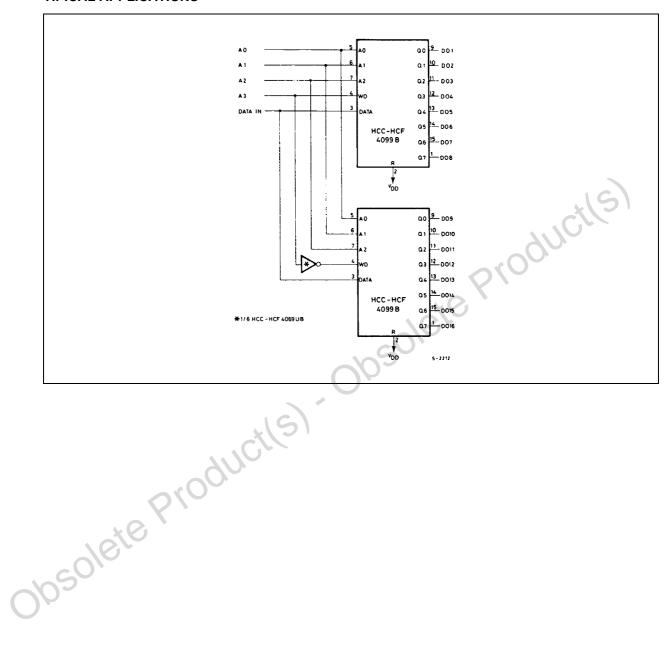
WAVEFORM 6: INPUT WAVEFORMS (f=1MHz; 50% duty cycle)



TIPICAL APPLICATIONS

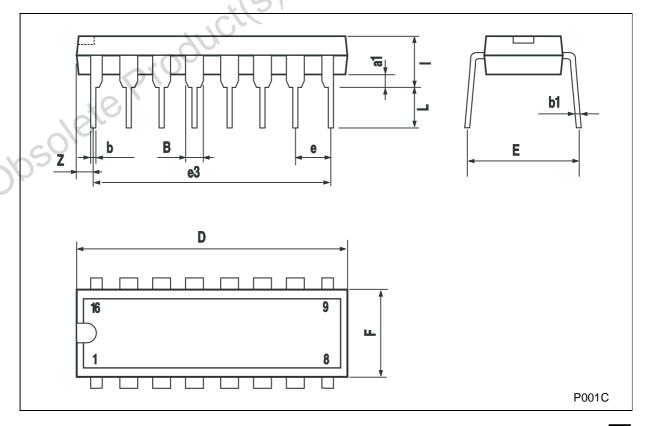


TIPICAL APPLICATIONS



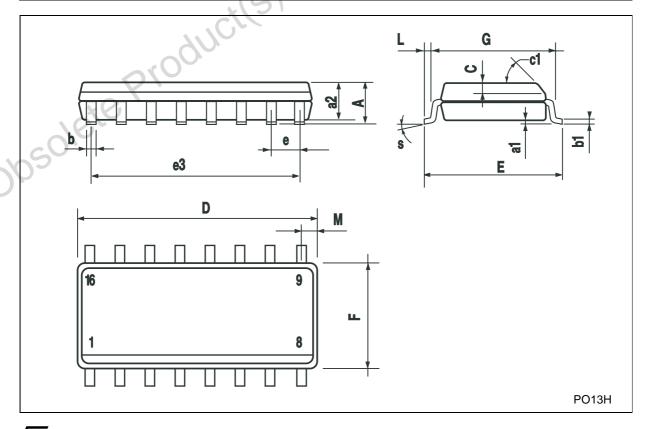
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010	16)		
D			20		.(0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78		20	0.700			
F			7.1	76/2		0.280		
I			5.1	0.		0.201		
L		3.3	Oh		0.130			
Z			1.27			0.050		



SO-16 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019	(15)		
c1			45° (typ.)	,(11		
D	9.8		10	0.385	YO.	0.393		
E	5.8		6.2	0.228	100	0.244		
е		1.27			0.050			
e3		8.89		46	0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			g° (m	nax.)	1			





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